

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Wolfgang STOLZ et al.

Art Unit: not yet assigned

Application No.: 10/580,653

Examiner: not yet assigned

Filed: 05/25/2006

Attorney Dkt. No.: 12007-0074

For: OPTICALLY PUMPED SEMICONDUCTOR DEVICES FOR THE GENERATION
OF RADIATION, THEIR PRODUCTION AS WELL AS METHODS FOR THE
STRAIN COMPENSATION IN THE LAYER SUCCESSIONS USED WITHIN

INFORMATION DISCLOSURE STATEMENT

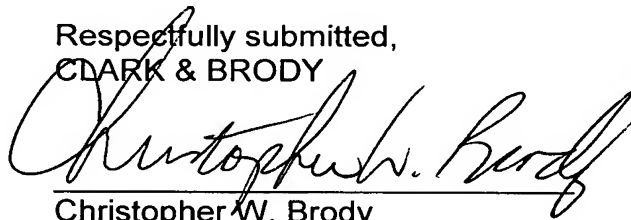
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

Applicants respectfully submit that this disclosure is being filed in accordance with 37 C.F.R. 1.97(b), therefore, no fee is required.

Respectfully submitted,
CLARK & BRODY



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Docket No.: 12007-0074
Date: April 20, 2007

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>	ATTY. DOCKET NO. 12007-0074	SERIAL NO. 10/580,653
	APPLICANT Wolfgang STOLZ et al.	
	FILING DATE 05/25/2006	GROUP ART UNIT Not yet assigned

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
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FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	<u>TRANSLATION</u> YES NO PART.
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OTHER REFERENCES *(Including Author, Title, Date, Pertinent Pages, Etc.)*

1.	C. Ellmers, et al., "GaAs-based VCSEL-structures with strain-compensated (GaIn)As/Ga(PAs)-MQWH active regions grown by using TBAs and TBP", Journal of Crystal Growth 195 (1998) 630-636
2.	C. Ellmers, et al., "Optically pumped (GaIn)As/Ga(PAs) vertical-cavity surface-emitting lasers with optimized dynamics", American Institute of Physics; Applied Physics Letters, Volume 74, No. 10, March 8, 1999, pgs. 1367-1369
3.	Y. Okuno, et al., "1.3 μm wavelength vertical cavity surface emitting laser fabricated by orientation-mismatched wafer bonding: A prospect for polarization control", American Institute of Physics; Applied Physics Letters, Volume 82, No. 15, April 14, 2003, pgs. 2377-2379
4.	S. Ae, et al., "Low threshold $\lambda = 1.3 \mu\text{m}$ multi-quantum well laser diodes grown by metalorganic vapor phase epitaxy using tertiarybutylarsine and tertiarybutylphosphine precursors", Journal of Crystal Growth 145 (1994) 852-857
5.	I. Kim, et al., "Composition control of InGaAsP in metalorganic chemical vapor deposition using tertiarybutylphosphine and tertiarybutylarsine ¹ ", Journal of Crystal Growth 193 (1998) 293-299
6.	A. Ougazzaden, et al., "High performance strained MQW lasers at 1.3 μm by MOVPE using arsine generator system", ELECTRONIC LETTERS, Vol. 30, No. 20, September 29, 1994, pgs. 1681-1682
7.	H.Q. Hou, et al., "High-Performance 1.06- μm Selectively Oxidized Vertical-Cavity Surface-Emitting Lasers with InGaAs-GaAsP Strain-Compensated Quantum Wells", IEEE Photonics Technology Letters, Vol. 9, No. 8, August 1997, pgs. 1057-1059

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.